

DESCRIPTION

The 82S12/112 is a Schottky TTL 32 bit multipoint memory organized in 8 words of 4 bits each. The device is ideally suited for high speed accumulators and buffer memories.

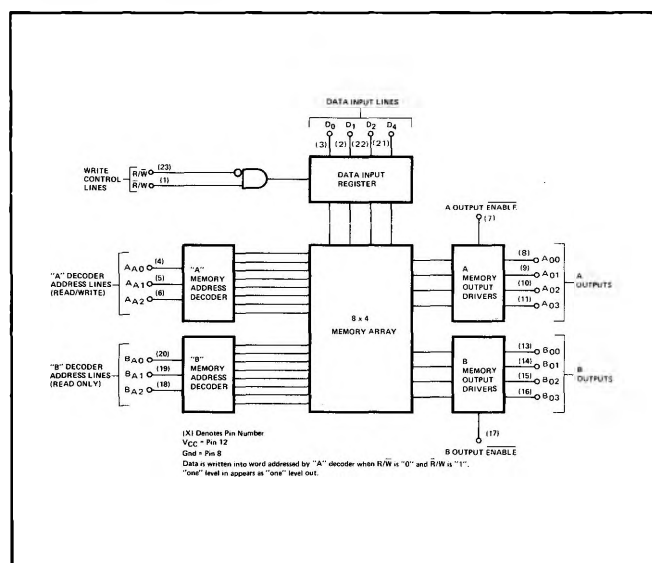
Stored data is addressed through 2 independent sets of 3-input decoders, and read out when the corresponding output enable line is low. Two separate word locations can, therefore, be read at the same time by enabling both the A and B output drivers. In addition, data can be read and written at the same time by utilizing the "A" address to specify the location of the word to be written, and the "B" address to specify the word to be read.

The 82S12/112 can be used in larger memory arrays since it includes all the control logic required to disable the chip and the outputs are open-collector devices suitable for "Wire-ORing."

FEATURES

- LOW CURRENT INPUT BUFFERS ($\sim 25\mu A$ TYPICAL)
- SEPARATE INPUT DECODERS FOR EACH WORD
- SEPARATE OUTPUT ENABLE LINES FOR EACH WORD
- OPEN COLLECTOR (82S12) OR TRI-STATE (82S112) OUTPUTS
- 2 WRITE ENABLE LINES
- FAST ACCESS (20 ns TYPICAL)
- USEFUL 8×4 ORGANIZATION
- TTL COMPATIBLE
- NON INVERTING DATA LINES

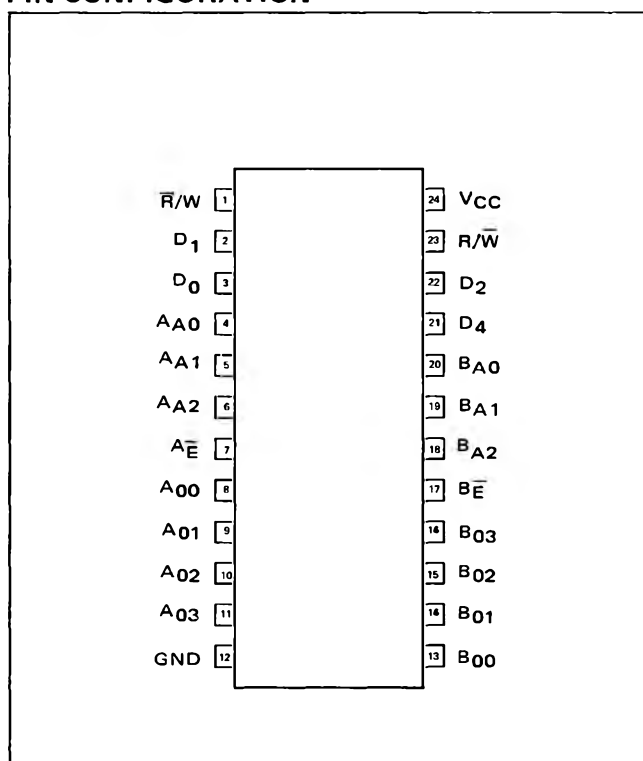
BLOCK DIAGRAM



APPLICATIONS

- SCRATCH PAD MEMORY
- BUFFER MEMORY
- ACCUMULATOR REGISTER
- GENERAL REGISTER

PIN CONFIGURATION



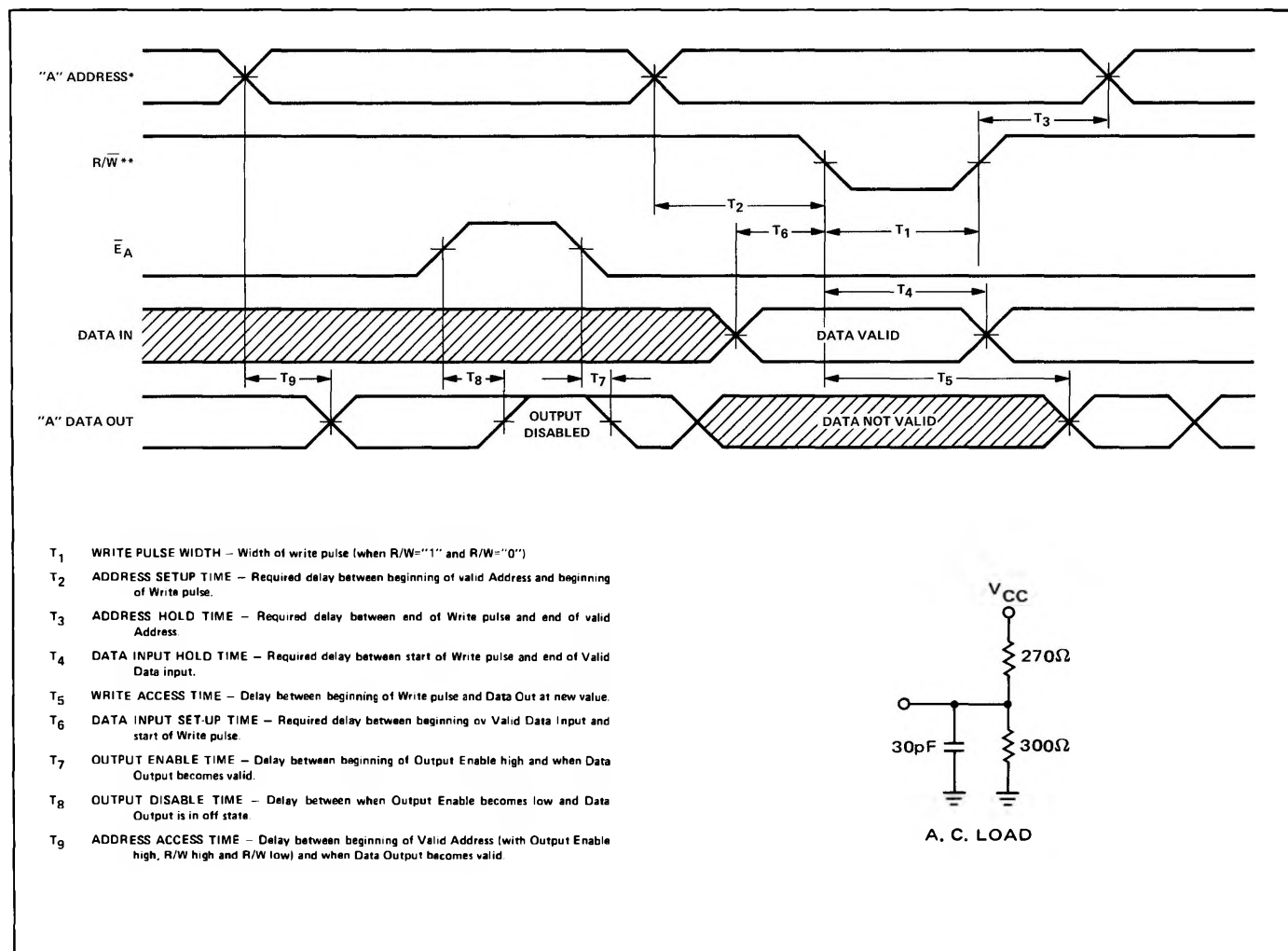
TRUTH TABLE

R/W	R/W	A OUTPUT ENABLE	B OUTPUT ENABLE	MODE	OUTPUTS	
					A	B
0	X	1	1	Outputs Disabled	"1"	"1"
0	X	1	0	Read	"1"	Data
0	X	0	1	Read	Data	"1"
0	X	0	0	Read	Data	Data
1	1	1	1	Read	"1"	"1"
1	1	1	0	Read	"1"	Data
1	1	0	1	Read	Data	"1"
1	1	0	0	Read	Data	Data
1	0	1	1	Write	"1"	"1"
1	0	1	0	Write	"1"	Data
1	0	0	1	Write	Data	"B" Address
1	0	0	0	Write	Data Being Written	Data Being "B" Written Address

OBJECTIVE ELECTRICAL SPECIFICATIONS $0^{\circ}\text{C} \leq T_A \leq 75^{\circ}\text{C}$; $-4.75\text{ V} \leq V_{CC} \leq 5.25\text{ V}$.

CHARACTERISTICS	LIMITS			UNITS	TEST CONDITIONS
	MIN.	TYP.	MAX.		
Input "0" Current			-250	μA	$V_{in} = 0.45\text{ V}$
Input "1" Current			25	μA	$V_{in} = 5.5\text{ V}$
Input "0" Threshold Voltage			0.85	V	
Input "1" Threshold Voltage	2.0			V	
Input Clamp Voltage	-1.2			V	
Output "0" Current	16			mA	$I_{in} = -18\text{ mA}$
Output "0" Current	9.6				$V_{out} = 0.5\text{ V}$
Output "1" Voltage (82S112)	2.6			Volts	$V_{out} = 0.45\text{ V}$
Output Off Current (82S12)			40	μA	$I_{out} = -3.2\text{ mA}$
Output Off Current (82S112)	-40		+40	μA	$V_{out} \leq 5.5\text{ V}$
Power Consumption		110/550	160/840	mA/mW	$0.45 \leq V_{out} \leq 5.5\text{ V}$
Write Pulse Width T_1		15	30	ns	Outputs Enabled
Address Set Up Time T_2		10	45	ns	$T_A = 25^{\circ}\text{C}$ Only
Address Hold Time T_3		0		ns	$0^{\circ}\text{C} \leq T_A \leq 75^{\circ}\text{C}$
Data Input Hold Time T_4		15		ns	
Write Access Time T_5		30		ns	
Data Input Set Up Time T_6		5		ns	
Output Enable Time T_7		10	20	ns	
Output Disable Time T_8		10	20	ns	
Address Access Time T_9		20	30	ns	

TIMING DIAGRAM



NOTES

***B** Address functions identically in read mode. No write mode through B address decoder.

**R/W input is either the reverse of R/W or held high.

Outputs can be disabled during write cycle to penetrate a known output state during write.